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SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR

(AUTONOMOUS)

B.Tech II Year I Semester Regular Examinations Feb-2021**ELECTRONIC DEVICES AND CIRCUITS**

(Common to ECE & EEE)

Time: 3 hours

Max. Marks: 60

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

- 1 a Explain about Diode resistances and determine the expression for forward dynamic resistance. **8M**
 b Examine the forward resistance of a PN junction diode when the forward current is 5mA at T = 300 K. Assume Silicon diode. **4M**

OR

- 2 a List the application of PN junction and Zener diodes. **4M**
 b Determine the expression for Diffusion capacitance of a PN Junction Diode. **8M**

UNIT-II

- 3 a Draw the circuit diagram of Full wave rectifier with inductor filter and illustrate its operation. Also derive the expression for ripple factor. **7M**
 b Find the value of inductance to be used in the inductor filter connected to a full wave rectifier operating at 60 Hz to provide a dc output with 4% ripple for a 100Ω load. **5M**

OR

- 4 a Explain dynamic scattering LCD and field effect LCD working with neat diagrams. **7M**
 b Explain working principle and characteristics of LED with neat diagram. Also list the applications of LED. **5M**

UNIT-III

- 5 a Explain the current components of PNP transistor and deduce the definitions of Emitter Efficiency, Base Transportation Factor and Large signal current gain. **7M**
 b With neat diagram, Interpret the Input and Output characteristics of a BJT in CB Configuration. **5M**

OR

- 6 Interpret the operation and characteristics of n-channel depletion type MOSFET with diagram. **12M**

UNIT-IV

- 7 a Define Transistor Biasing and explain the need for Biasing. **5M**
 b Explain the concept of DC and AC Load lines and discuss the criteria for fixing the Q-point. **7M**

OR

- 8 a Estimate the stability factors S, S' and S'' of a BJT Voltage Divider bias. **12M**

UNIT-V

- 9 Summarize the expressions for input impedance, output impedance and voltage gain of JFET Common Drain amplifier with neat diagram. **12M**

OR

- 10 For a CB transistor amplifier driven by a voltage source of internal resistance $R_s = 1200\Omega$, the load Impedance of $R_L = 1000\Omega$. The h parameters are $h_{ib} = 22\Omega$, $h_{rb} = 3 \times 10^{-4}$, $h_{fb} = -0.98$, $h_{ob} = 0.5\mu A/V$. Find current gain, voltage gain, input impedance and output impedance using exact analysis and approximate analysis. **12M**

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